

CP336V-2N5551

NPN - High Voltage Transistor Die

The CP336V-2N5551 is a silicon NPN transistor designed for high voltage, general purpose applications.



MECHANICAL SPECIFICATIONS:

Die Size	17.3 x 17.3 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Size	3.9 x 3.9 MILS
Emitter Bonding Pad Size	3.9 x 3.9 MILS
Top Side Metalization	Al-Si – 17,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	1.8 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	57,735

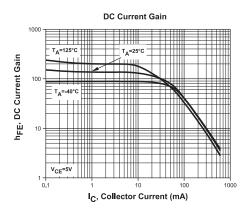
	RATINGS: (T _A =25°C)	SYMBOL	180	UNITS V
Collector-Base Voltage Collector-Emitter Voltage		V _{CBO} V _{CEO}	160	V
Emitter-Base Voltage		V _{EBO}	6.0	V
Continuous Collector Current		IC FBO	600	mA
Operating and Storage Junction Temperature		T _J , T _{stg}	-65 to +150	°C
ELECTRICA SYMBOL	L CHARACTERISTICS: (T _A =25°C) TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =120V		50	nA
I _{EBO}	V _{EB} =4.0V		50	nA
BV _{CBO}	I _C =100μA	180		V
BV _{CEO}	I _C =1.0mA	160		V
BV_{EBO}	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.15	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.20	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA		1.0	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	80		
hFE	V _{CE} =5.0V, I _C =10mA	80	250	
h _{FE}	V _{CE} =5.0V, I _C =50mA	30		
f_T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
C_{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		6.0	pF

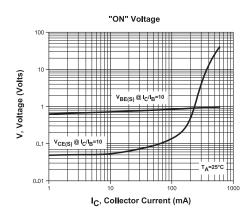
CP336V-2N5551

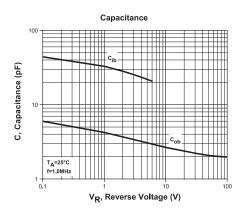
Typical Electrical Characteristics

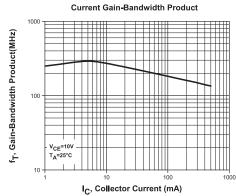


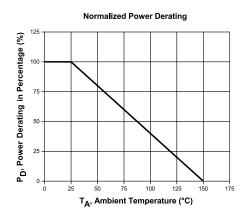
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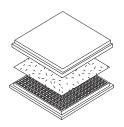






BARE DIE PACKING OPTIONS

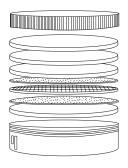




BARE DIE IN TRAY (WAFFLE) PACK

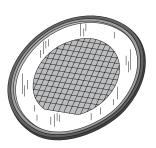
CT: Singulated die in tray (waffle) pack. (example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes). (example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked. (example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,

100% tested with reject die inked. (example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications: www.centralsemi.com/bdspecs

R2 (3-April 2017)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- · Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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